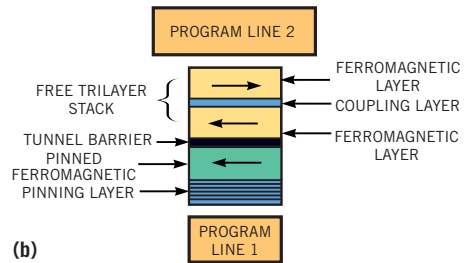
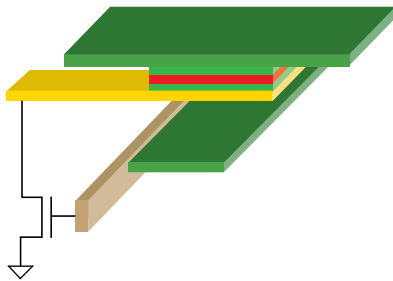


(a)

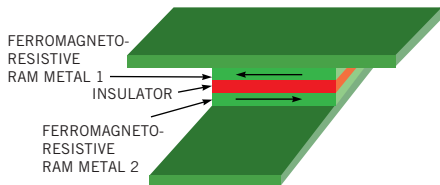


(b)

**Figure 4**



(c)



(d)

**A commonplace MRAM cell is susceptible to disturbance from nearby cells' program and erase operations (a), whereas an advanced cell design is more immune to these effects (b). Conventional (c) and crosspoint (d) cells have different cost and performance characteristics, suitable for diverse applications (a and b courtesy Freescale, c and d courtesy Infineon).**